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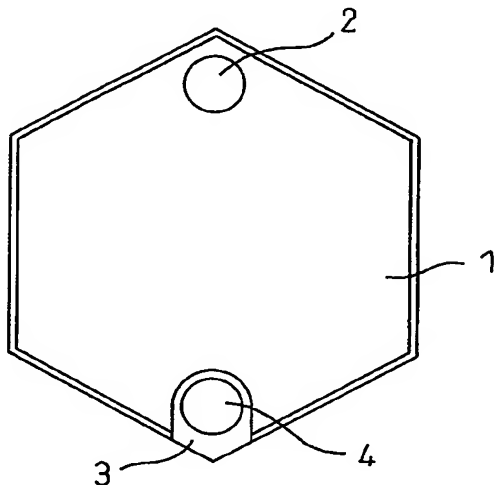
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(54) Title: PRODUCTION METHOD FOR SEMICONDUCTOR DEVICE



(57) Abstract: An object of the present invention is to provide a method of producing a Group III nitride semiconductor device having a chip form which is pentagonal or more highly polygonal maintaining good area efficiency and at a low cost. The inventive method of producing a Group III nitride semiconductor device having a chip shape which is a pentagonal or more highly polygonal shape comprises a first step of epitaxially growing a Group III nitride semiconductor on a substrate to form a semiconductor wafer; a second step of irradiating said semiconductor wafer with a laser beam to form separation grooves; a third step of grinding and/or polishing the main surface side differently from the epitaxially grown main surface of the substrate; and a fourth step of division into individual chips by applying stress to said separation grooves.

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